

2SJ112

SILICON P-CHANNEL MOS FET

**HIGH SPEED POWER SWITCHING,
HIGH FREQUENCY POWER AMPLIFIER**
Complementary pair with 2SK398

■ FEATURES

- Low On-Resistance.
- High Speed Switching.
- High Cutoff Frequency.
- No Secondary Breakdown.
- Suitable for Switching Regulator, DC-DC Converter, Motor Control, and Ultrasonic Power Oscillators.

■ ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)

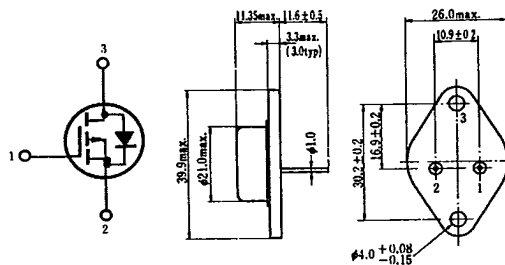
Item	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-100	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current	I_D	-10	A
Drain Peak Current	$I_{D(pk)}$	-15	A
Body-Drain Diode Reverse Drain Current	I_{DR}	-10	A
Channel Dissipation	P_{ch}^*	100	W
Channel Temperature	T_{ch}	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 ~ +150	$^\circ\text{C}$

*Value at $T_c=25^\circ\text{C}$

■ ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$)

Item	Symbol	Test Condition	min.	typ.	max.	Unit
Drain-Source Breakdown Voltage	$V_{(BR)DS}$	$I_D=-10\text{mA}$, $V_{GS}=0$	-100	—	—	V
Gate-Source Leak Current	I_{GSS}	$V_{GS}=\pm 20\text{V}$, $V_{DS}=0$	—	—	± 1	μA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-80\text{V}$, $V_{GS}=0$	—	—	-1	mA
Gate-Source Cutoff Voltage	V_{GSOFF}	$I_D=-1\text{mA}$, $V_{DS}=-10\text{V}$	-2.0	—	-5.0	V
Static Drain-Source on State Resistance	$R_{DS(on)}$	$I_D=-5\text{A}$, $V_{GS}=-15\text{V}^*$	—	0.25	0.35	Ω
Drain-Source Saturation Voltage	$V_{DS(sat)}$	$I_D=-5\text{A}$, $V_{GS}=-15\text{V}^*$	—	-1.25	-1.75	V
Forward Transfer Admittance	$ y_{fs} $	$I_D=-5\text{A}$, $V_{DS}=-10\text{V}^*$	1.5	2.0	—	S
Input Capacitance	C_{iss}	$V_{DS}=-10\text{V}$, $V_{GS}=0$, $f=1\text{MHz}$	—	1100	—	pF
Output Capacitance	C_{oss}		—	650	—	pF
Reverse Transfer Capacitance	C_{rss}		—	90	—	pF
Turn-on Delay Time	$t_{A(on)}$	$I_D=-2\text{A}$, $V_{GS}=-15\text{V}$ $R_L=15\Omega$	—	20	—	ns
Rise Time	t_r		—	50	—	ns
Turn-off Delay Time	$t_{A(off)}$		—	90	—	ns
Fall Time	t_f		—	70	—	ns
Body-Drain Diode Forward Voltage	V_{DF}	$I_F=-5\text{A}$, $V_{GS}=0$	—	-0.9	—	V
Body-Drain Diode Reverse Recovery Time	t_{rr}	$I_F=-5\text{A}$, $V_{GS}=0$ $di_F/dt=50\text{A}/\mu\text{s}$	—	250	—	ns

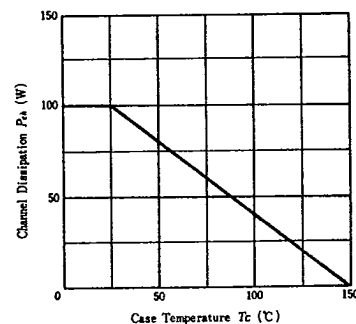
*Pulse Test



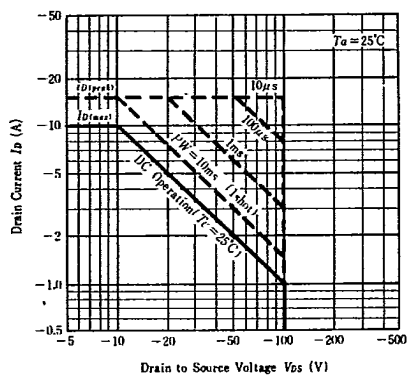
1. Gate
2. Source
3. Drain
(Case)
(Dimensions in mm)

(JEDEC TO-3)

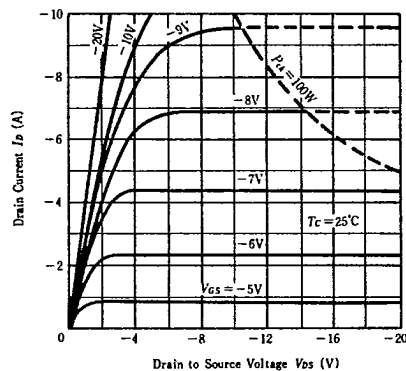
POWER VS. TEMPERATURE DERATING



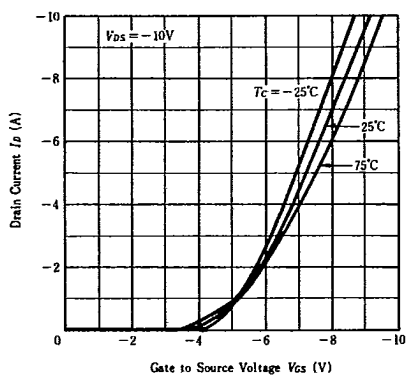
MAXIMUM SAFE OPERATION AREA



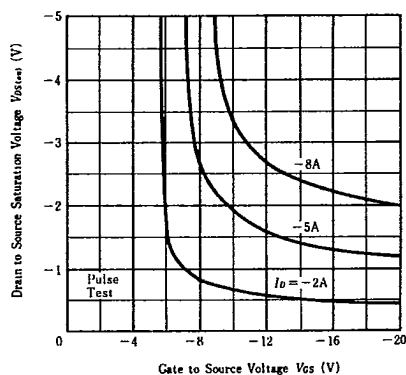
TYPICAL OUTPUT CHARACTERISTICS



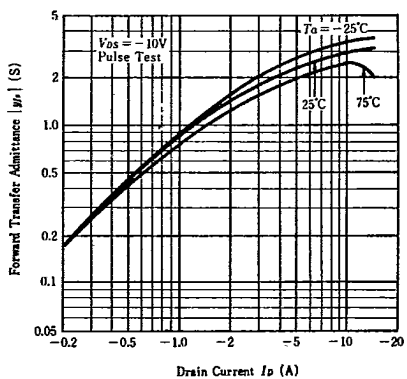
TYPICAL TRANSFER CHARACTERISTICS



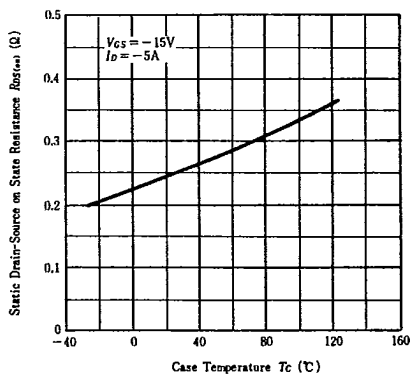
DRAIN-SOURCE SATURATION VOLTAGE VS. GATE-SOURCE VOLTAGE



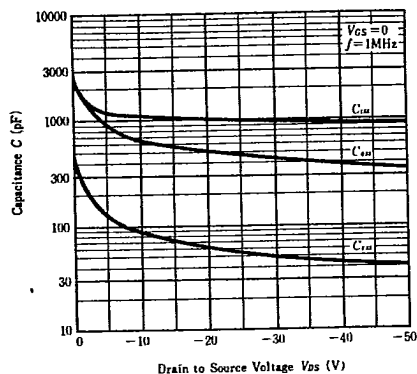
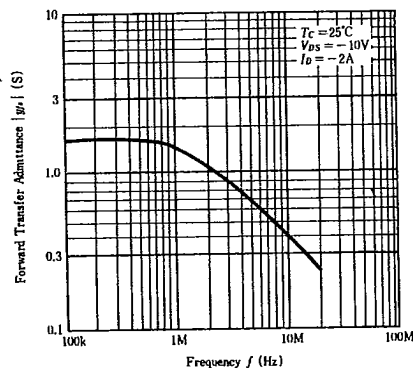
FORWARD TRANSFER ADMITTANCE VS. DRAIN CURRENT



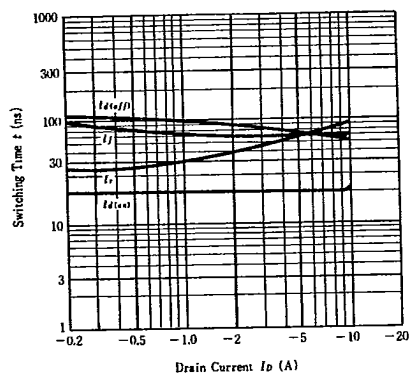
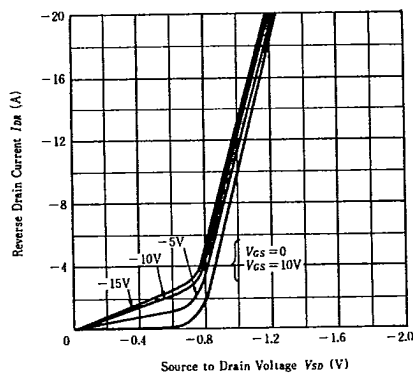
STATIC DRAIN-SOURCE ON STATE RESISTANCE VS. TEMPERATURE



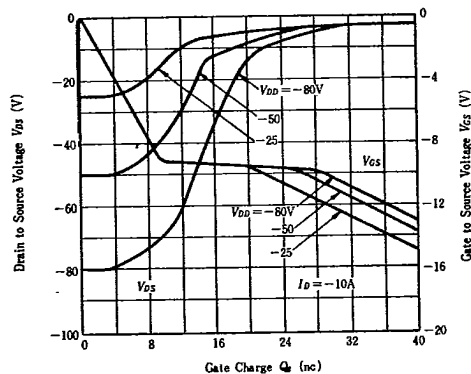
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TYPICAL CAPACITANCE VS.
DRAIN-SOURCE VOLTAGEFORWARD TRANSFER ADMITTANCE
VS. FREQUENCY

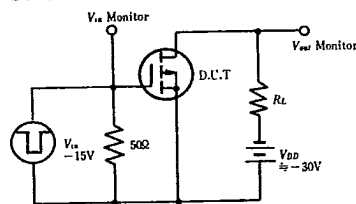
SWITCHING CHARACTERISTICS

MAXIMUM BODY-DRAIN DIODE
FORWARD VOLTAGE

DYNAMIC INPUT CHARACTERISTICS



SWITCHING TIME TEST CIRCUIT



WAVEFORMS

